

AMENDMENTS TO THE SPECIFICATION

Kindly amend paragraph [0042] as follows:

In the next step, shown in Figure 2(h), the oxide 120 and the dopant source material 115 are stripped by, for example, a conventional wet process with HF species. The etch chemistry may include buffered HF (BHF), dilute HF (DHF) or concentrated HF. Alternatively, the oxide may be stripped by a conventional dry etch process. Note that the trench surface area is enlarged following oxide strip, thereby enhancing trench capacitance. Other trench capacitance enhancement approaches also may be practiced at this point in the process, such as formation of HSG in the lower trench region that is not covered by the collar 119, wet or dry etching the lower trench that is not covered by the collar 119 to form a bottle-shape in the lower trench, gas phase doping (GPD), plasma doping, plasma immersion ion implantation, or any combination of these approaches. The etchant for wet etching the substrate may contain ammonia, KOH, or HF:HNO₃:CH₃COOH. The use of KOH may cause K contamination, so an additional cleaning step may be required. The etchant for dry wet-etching the substrate may contain Cl₂ plasma.